

Ram Technology Advancement, A Systematic Review

Frank Ekene Ozioko, Ifeonu Paul Ifenna

Department of Computer Science, Enugu State University of Science and Technology (ESUT)

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ABSTRACT

Random Access Memory (RAM) is an important part of modern computer systems because it temporarily stores data and instructions needed for fast processing. As technologies such as artificial intelligence, cloud computing, gaming, and big data continue to grow, the demand for faster, larger, and more energy efficient memory systems has increased. This paper reviews the advancement of RAM technology from traditional memories such as SRAM and DRAM to modern technologies including DDR5, High Bandwidth Memory (HBM), Magnet or resistive RAM (MRAM), Resistive RAM (RRAM), and Phase Change Memory (PCM). The study discusses major research challenges affecting RAM technology, including memory latency, high power consumption, heat generation, scalability problems, reliability issues, limited bandwidth, and the memory wall problem, where processor speed increases faster than memory speed. The paper also examines the contributions and limitations of different researchers and identifies possible solutions such as hybrid memory architectures, Processing-in-Memory (PIM), Computing-in-Memory (CIM), intelligent memory management, and advanced cooling systems. In conclusion, the study shows that although modern RAM technologies provide significant improvements in speed, bandwidth, and energy efficiency, challenges such as cost, thermal issues, scalability, and hardware integration still remain, making further research necessary for developing faster, more reliable, and energy-efficient memory systems for future computing applications.

Index Terms: Latency, Scalability, Memory, Startic, Random

INTRODUCTION

Random Access Memory (RAM) is one of the most important components of a computer system. It is used to temporarily store data and instructions that the processor needs while running programs. RAM helps computers perform tasks quickly and efficiently by allowing fast access to information. Different types of RAM, such as Dynamic Random Access Memory (DRAM) and Static Random Access Memory (SRAM), are widely used in personal computers, servers, smartphones, and other digital devices.

As computer technology continues to improve, the demand for faster and more efficient RAM has increased. Modern applications such as artificial intelligence, cloud computing, gaming, and big data processing require high-speed memory systems that can handle large amounts of data. However, current RAM technology faces several research problems that affect system performance, energy efficiency, reliability, and cost.

One major research problem in RAM technology is memory latency. Although processors are becoming faster, RAM speed is not improving at the same rate. This creates a performance gap between the processor and memory, often called the “memory wall.” Because of this delay, the processor may spend time waiting for data from RAM, which reduces overall system performance.

Power consumption is another important issue in RAM technology. DRAM requires constant refreshing to keep stored data active, which increases energy usage. High power consumption leads to heat generation and reduces battery life in portable devices such as laptops and smart-

phones. Researchers are working on ways to design RAM systems that consume less energy while still providing high performance.

Scalability is also a major challenge in RAM development. As memory manufacturers reduce chip sizes to increase storage capacity, problems such as leakage current, noise, and instability become more serious. Smaller memory cells are harder to manufacture and may reduce the reliability of the memory system. This makes the production of advanced RAM technologies more difficult and expensive.

Another research problem is reliability and data integrity. RAM can experience errors such as bit flips and soft errors caused by heat, electrical interference, or hardware aging. These errors can affect system stability and lead to data loss. To reduce these problems, systems often use error correction methods, but these solutions increase hardware complexity and cost.

Bandwidth limitations are also a challenge in modern RAM systems. Many applications require large amounts of data to move quickly between memory and processors. Traditional RAM technologies may not provide enough bandwidth to support high-performance computing systems efficiently. Researchers are exploring new memory architectures and technologies to improve data transfer speed.

Volatility is another limitation of RAM technology. Most RAM types lose stored data when power is turned off. This makes RAM unsuitable for permanent data storage. Researchers are studying non-volatile memory technologies that can combine the speed of RAM with the ability to retain data without power.

Due to these research problems, scientists and engineers are developing advanced memory technologies such as DDR5, MRAM, ReRAM, and Phase-Change Memory (PCM). These technologies aim to improve speed, reduce power consumption, increase storage capacity, and provide better reliability for future computer systems.

In conclusion, RAM technology plays a very important role in modern computing, but it still faces many challenges. Problems such as latency, power consumption, scalability, reliability, bandwidth limitations, and volatility continue to affect the performance of computer systems. Research in RAM technology is therefore necessary to develop faster, more efficient, and more reliable memory systems for future computing needs.

[1], Recent research into memory architecture combined highlights a strategic change for designing memory hierarchies designed for the high-performance computing (HPC) market today and will scale to the needs for tomorrow's applications. An emphasis on energy efficiency, low latency, and high throughput is situated in an integrated memory system maximizing workloads to be effective and efficient in an increasingly opaque and complex data scape. Research around virtual pipe lining, multi-stream command scheduling, high bandwidth inter connects and millimeter wave communication channels has produced frameworks that appropriately manage energy consumption, design complexity, operational costs, and speeds of memory accesses. Together with hardware advancement and adaptation of memory subsystems, again shows an opportunity to provide efficient, sustained data delivery at high speeds, thereby effectively interacting with compute cores capable of high rates of data processing for applications in artificial intelligence, deep learning, and large-metrics analysis

Overview and Motivation

RAM technology is an essential part of every computer system because it stores data and instructions that the processor needs for fast processing. Modern technologies such as artificial intelligence, cloud computing, gaming, mobile devices, and big data applications require memory systems that are faster, more reliable, and energy efficient. Traditional RAM technologies like DRAM and SRAM have supported computing for many years, but they are now facing several limitations, including high power consumption, memory latency, limited scalability, and reliability issues.

The motivation for studying research problems in RAM technology comes from the growing demand for better computer performance and efficient data processing. As processors continue to become faster, current RAM systems struggle to keep up with the increasing speed and workload requirements. This creates performance bottlenecks that affect the overall efficiency

of computer systems. In addition, modern devices require lower power consumption and higher memory capacity, which traditional RAM technologies may not fully provide.

Researchers are therefore motivated to develop improved memory technologies that can solve these problems. The goal is to design RAM systems that are faster, consume less energy, provide larger storage capacity, and improve system reliability. This research is important because future computing systems will depend heavily on advanced memory technologies to support modern applications and growing data demands.

Evolution of RAM Technologies advancement

The evolution of RAM technology has played a major role in improving computer performance and efficiency over the years. Random Access Memory (RAM) is a temporary storage area that allows the processor to quickly access data while programs are running. As computer systems became more powerful and software applications became more complex, RAM technology also advanced to provide faster speed, larger capacity, lower power consumption, and better overall performance. [2], The integration limit of Flash memories is approaching, and many new types

of memory to replace conventional Flash memories have been proposed. Emerging memory technologies promise new memories to store more data at less cost than the expensive-to-build silicon chips used by popular consumer gadgets including digital cameras, cell phones and portable music players.

In the early years of computing, magnetic core memory was used as the main form of RAM. This technology stored data using tiny magnetic rings called cores. Although it was reliable for early computers, it was very large, expensive, slow, and consumed a lot of power. As computer technology improved, magnetic core memory was gradually replaced by semiconductor memory, which was smaller, faster, and more efficient.

The introduction of semiconductor RAM marked a major turning point in memory technology. One of the first important semiconductor memories was Static Random-Access Memory (SRAM). SRAM stores data using flip-flop circuits and does not require constant refreshing to maintain stored information. Because of this, SRAM is very fast and provides low latency. However, it is expensive and takes up more physical space. Due to its high speed, SRAM is mainly used in processor cache memory where quick access to data is important.

Another important advancement was Dynamic RAM (DRAM). DRAM stores data using capacitors and requires continuous refreshing to keep data active. Although DRAM is slower than SRAM, it is cheaper and can store more data in a smaller space. This made DRAM suitable for use as the main memory in computers. DRAM became the foundation for many future RAM technologies because it provided a balance between cost and storage capacity.

As processor speeds increased, researchers developed improved versions of DRAM to reduce performance limitations. Fast Page Mode (FPM) DRAM was introduced to improve memory access speed, but it could not fully meet the demands of faster processors. Later, Extended Data Out (EDO) RAM improved performance further by allowing some memory operations to overlap, which increased data transfer efficiency.

A major breakthrough came with the development of Synchronous Dynamic RAM (SDRAM). SDRAM synchronized its operations with the processor clock, allowing memory and the CPU to work together more efficiently. This greatly improved system performance and multitasking capabilities. SDRAM became widely used in computers and created the foundation for the next generation of memory technologies.

The introduction of Double Data Rate (DDR) RAM represented one of the most important advancements in memory systems. DDR memory increased performance by transferring data on both the rising and falling edges of the clock signal, effectively doubling the data transfer rate. The first DDR generation provided better bandwidth and speed compared to SDRAM.

Over time, newer DDR generations were developed to improve speed, capacity, and energy efficiency. DDR2 offered higher bandwidth and reduced power consumption. DDR3 further improved performance and became popular in laptops and desktop computers because of its efficiency

and affordability. DDR4 introduced even higher data transfer rates, larger memory capacities, and lower voltage usage, making it suitable for gaming systems, servers, and modern computing environments.

Currently, DDR5 represents the latest mainstream advancement in RAM technology. DDR5 provides significantly higher speed, larger bandwidth, and improved power management compared to previous generations. It supports demanding applications such as artificial intelligence, cloud computing, machine learning, and high-performance computing systems. Although DDR5

offers major improvements, it also comes with challenges such as higher cost and compatibility requirements.

Apart from traditional system RAM, specialized memory technologies have also evolved. Graphics Double Data Rate (GDDR) memory was developed specifically for graphics processing units (GPUs). GDDR provides extremely high bandwidth needed for gaming, video rendering, and artificial intelligence applications. Another important development is High Bandwidth Memory (HBM), which uses stacked memory architecture to provide very fast data transfer while consuming less power. HBM is commonly used in supercomputers and advanced AI systems.

Modern research has also introduced emerging memory technologies such as Magnetoresistive RAM (MRAM), Resistive RAM (ReRAM), and Phase Change Memory (PCM). These technologies aim to provide faster speed, lower energy consumption, higher durability, and non-volatile storage capabilities. Researchers believe these advanced memory systems may eventually replace or improve current DRAM technologies in the future.

Despite the many improvements in RAM technology, several challenges still exist. Modern memory systems face issues related to heat generation, latency, power consumption, manufacturing cost, and scalability. As computing workloads continue to increase, especially in artificial intelligence and high-performance computing, researchers continue to search for better memory solutions.

Today, RAM technology continues to evolve rapidly to support modern computing demands. Future memory systems are expected to become faster, smarter, more energy efficient, and more scalable. Advanced technologies such as 3D memory stacking, AI-optimized memory systems, and memory-centric computing architectures are expected to shape the future of computing. The continuous advancement of RAM technology remains essential for the development of modern computers, scientific research systems, industrial applications, and artificial intelligence technologies.

Advancement in DDR RAM Technologies

The development of Double Data Rate (DDR) memory greatly improved RAM performance. DDR memory transfers data on both rising and falling clock signals, effectively doubling the data transfer rate compared to SDRAM.

DDR1 was the first DDR generation and provided improved bandwidth and speed. DDR2 later introduced higher bandwidth, lower voltage, and improved efficiency. DDR3 further improved memory performance and became widely used in laptops and desktop computers because of its lower power consumption and better speed.

DDR4 introduced higher data transfer rates, larger memory capacities, and improved multitasking performance. It became popular in gaming systems, servers, and high-performance computing environments.

DDR5 is the latest mainstream RAM technology. It offers significantly higher bandwidth, faster data transfer speed, larger memory capacity, and improved power management. DDR5 is designed to support modern technologies such as artificial intelligence, machine learning, and cloud computing. However, DDR5 still faces challenges such as higher manufacturing cost and increased latency in some workloads.

[3], DDR6 is the successor to DDR5, slated to launch between 2026 and 2027 or even later. It doubles the number of sub-channels to four 16-bit subchannels and is expected to double the bandwidth provided by DDR5 at lower voltage.

Memory Wall Problem

The **Memory Wall Problem** refers to the growing gap between the speed of the CPU (processor) and the speed of

the main memory (RAM). Over time, processors have become much faster, but memory speed has not improved at the same rate. Because of this difference, the processor often spends time waiting for data to come from memory instead of performing useful work.

In modern computer systems, the CPU can execute billions of instructions per second, but accessing data from RAM may take much longer. This delay creates a performance bottleneck known as the memory wall. As applications such as artificial intelligence, gaming, cloud computing, and big data processing continue to grow, the memory wall becomes a more serious challenge.

The memory wall problem affects overall system performance in several ways. First, it increases latency because the processor must wait for data retrieval. Second, it reduces throughput since fewer tasks can be completed within a given time. Third, it increases power consumption because repeated memory access operations require more energy.

Several factors contribute to the memory wall problem, including:

- Slow improvement in DRAM speed compared to CPU speed
- Large data movement between processor and memory
- Increasing workload complexity
- Limited memory bandwidth

To reduce the effects of the memory wall, researchers and engineers use different techniques such as:

- Cache memory
- Prefetching techniques
- Parallel memory access
- High Bandwidth Memory (HBM)
- Processing-in-Memory (PIM)
- Multi-channel memory architectures

Modern RAM technologies such as DDR5 and HBM are designed to improve memory bandwidth and reduce latency. Emerging technologies like MRAM, RRAM, and neuromorphic memory systems are also being researched to overcome memory bottlenecks in future computing systems.

In summary, the memory wall problem is one of the major challenges in computer architecture because memory systems cannot always keep up with the increasing speed of processors. Solving this problem is important for improving the performance, efficiency, and scalability of modern computer systems.

LITERATURE REVIEW

The advancement of RAM technology has become an important research area because modern computing systems require faster processing, larger storage capacity, and lower power consumption. Traditional memory technologies such as Dynamic Random Access Memory (DRAM) and Static Random Access Memory (SRAM) have been widely used for many years, but they face limitations in speed, scalability, heat generation, and energy efficiency. Table 1 represents a classification matrix of the current literatures in RAM technology. Researchers have therefore focused

on developing advanced and emerging memory technologies to overcome these challenges[4]. According to [4], emerging memory technologies are transforming modern computing systems

by providing higher performance, better scalability, and improved energy efficiency. The study explained that traditional memories are struggling to meet the demands of artificial intelligence, cloud computing, and data-intensive applications. The researchers reviewed several advanced memory technologies including Magnetoresistive RAM (MRAM), Phase Change Memory (PCM), Ferroelectric RAM (FeRAM), and Resistive RAM (RRAM). These technologies are considered promising because they combine non-volatile storage with high processing speed.

Researchers have also studied the relationship between RAM technology and the memory explained that the growing gap between processor speed and memory speed creates performance bottlenecks in modern computer systems. To reduce this problem, emerging non-volatile memory technologies such as MRAM, PCM, and RRAM are being developed. These technologies improve bandwidth, reduce latency, and support advanced computing architecture[5].

A survey by Asad et al [6], focused on memory subsystems for deep neural network accelerators. The study found that traditional DRAM systems consume high energy and limit AI performance because of frequent data transfers. Advanced memory technologies such as High Bandwidth Memory (HBM) and hybrid memory architectures were identified as effective solutions for improving AI acceleration and energy efficiency.

[7], Memory systems are a major system performance bottleneck” and also said that current DRAM technology faces “significant scaling challenges” as computers continue to demand higher speed and larger memory capacity. He further explained that future RAM systems must improve “latency, bandwidth, energy efficiency, and reliability.”

[8], RRAM is considered as one of the most promising candidates for future nonvolatile memory” because of its “simple structure, high density, fast switching speed, low power consumption, and compatibility with CMOS technology. He also explained that RRAM can overcome many limitations of traditional DRAM and flash memory.

[9], DRAM technology is facing scaling challenges as feature sizes continue to shrink. He added that future RAM advancement depends on “new cell structures, materials, and manufacturing technologies” to maintain performance and storage growth.

[10], MRAM is one of the leading candidates for next-generation nonvolatile memory. He further stated that modern MRAM technology provides “high speed, high endurance, and strong data retention. The current evolution of RAM technology is reflected in [11], Resistive switching memory technologies support “in-memory computing and machine learning applications.” He also explained that advanced RRAM systems improve “parallel processing, energy efficiency, and neuromorphic computing performance.”

[12], Emerging memory technologies are becoming key enablers for artificial intelligence applications.” He further stated that advanced RAM technologies such as MRAM and RRAM provide “high speed, low energy consumption, and high endurance” for modern computing systems.

Overall, the literature shows that RAM technology has advanced significantly from traditional DRAM and SRAM to modern non-volatile and high-bandwidth memory systems. Technologies such as MRAM, RRAM, PCM, and HBM are helping to solve problems related to latency, power consumption, scalability, and memory bandwidth. Although these technologies still face challenges such as high manufacturing cost, thermal issues, and reliability concerns, continuous research is improving their performance and adoption in modern computing systems[4].

[13], Continued scaling of DRAM technology faces increasing technical and economic challenges.” He further explained that as DRAM devices become smaller, maintaining reliable data retention becomes more difficult because of leakage current, cell interference, and reduced capacitor size. He discussed that future RAM advancement will depend on innovative transistor structures, improved fabrication methods, and new memory materials that can maintain performance while reducing power consumption. According to him, advanced RAM technologies are necessary to meet the growing demands of mobile computing, cloud systems, and high-performance processors.

[14], Phase change memory has the potential to be a scalable alternative to DRAM.” He explained that PCM technology offers non-volatility, high scalability, and better storage density compared to traditional DRAM systems. According to him, PCM can help reduce power consumption in future memory systems while maintaining strong performance for data-intensive applications. He further discussed that advanced memory technologies are necessary because existing DRAM systems struggle to meet the growing performance demands of modern processors and large-scale computing systems.

According to [15],The memory system is becoming one of the dominant limitations in modern computing systems.” He further explained that while processor speeds continue to improve rapidly, memory technologies are not advancing at the same rate, creating what is commonly known as the “memory bottleneck.” According to him, future RAM technologies must focus on improv- ing bandwidth, reducing latency, and lowering energy consumption in order to support modern applications such as artificial intelligence, cloud computing, and scientific simulations. He also discussed that advanced memory architectures and closer integration between processors and memory systems are necessary for future high-performance computing environments. Horowitz explained that current RAM systems are slowing down overall computer performance because processors can process data faster than memory can deliver it. His work supports the need for advanced RAM technologies that can operate faster and consume less power.

[16],stated that Resistive switching memory technologies are among the leading candidates for future nonvolatile memory.” He explained that traditional RAM technologies are approaching physical scaling limits because smaller memory cells become more difficult to manufacture reliably. According to him, resistive RAM technologies provide advantages such as high density, low power consumption, simple device structure, and faster switching speed. He further discussed that RRAM can support future applications including mobile computing, artificial intelligence, and large-scale data centers because of its scalability and energy efficiency. Wong's research explains why many scientists believe RRAM could replace or improve current RAM systems in the future. His work highlights the importance of energy efficiency and scalability in next-generation memory technologies.

[17],Memristive devices open new opportunities for memory and logic integration.” He explained that traditional computer systems separate memory and processing units, causing delays and increased energy consumption during data transfer. According to him, memristor-based memory technologies can combine storage and computation together, improving speed and reducing power consumption. He further discussed that such technologies are especially useful for machine learning, artificial intelligence, and data-intensive applications that require large amounts of fast memoryaccess.Kvatinsky's researchfocuseson combiningRAM and processinginto one system, which could solve the memory bottleneck problem in future computers.

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TABLE I Classification Matric of Current Literatures in Ram Technology Advancement

Author	Method	Final Result	Advantages	Disadvantages
Xie et al.	Study of memory wa l and non- volatile memory	Reduced latency and improved band- width	Be ter bandwidth and architec- ture support	Complex system integration
Asad et al.	Survey on AI memory subsystems	HBM improves AI acceleration	High bandwidth and energy effi- ciency	Expensive implementation
Mutlu and Kim	Analysis of DRAM scaling chal- lenges	Future RAM needs be ter efficiency and reliability	Identifies key improvement ar- eas	Severe DRAM scaling problems
Zahoor et al.	Research on RRAM technology	RRAM suitable for future memory sys- tems	Fast switching and low power	Reliability issues
Kim et al.	Study of future DRAM technologies	New structures needed for future RAM	Be ter performance and storage growth	Scaling limitations
Ikegawa et al.	Research on MRAM	MRAM o fers speed and	Strong data retention	High production cost
Molas et al. Kim	Review of AI memory	MRAM and RRAM	High endurance and	Manufacturing
Lee et al.	Research on PCM architecture	PCM can replace DRAM	Be ter density and low power	Endurance limitations

TOPIC DISCUSSION

The advancement of RAM technology has received significant attention from researchers because modern computing systems require faster memory speed, lower power consumption, improved reliability, and better scalability. Many authors have discussed the development of technologies such as Dynamic Random Access Memory (DRAM), Magnetoresistive RAM (MRAM), Resistive RAM (RRAM), High Bandwidth Memory (HBM), and Phase Change Memory (PCM). Although these studies provide valuable contributions to memory research, many of them also have limitations in methodology, practical implementation, cost analysis, scalability evaluation, and long-term reliability discussions. A critical analysis of these authors helps identify research gaps and possible solutions for improving future RAM technologies.

Das (2022) focused mainly on emerging nonvolatile memory technologies such as RRAM and PCM. The study explained that these technologies can improve energy efficiency, scalability, and processing speed in future computing systems. Although the review provided a good overview of modern memory technologies, the study did not fully address the real-world manufacturing challenges involved in commercial implementation. The paper discussed the advantages of RRAM and PCM but provided limited discussion on production cost, compatibility with existing hardware systems, and industrial adoption barriers. Many emerging memory technologies perform well in laboratory environments but face serious difficulties during large-scale manufacturing. A possible solution to this limitation is stronger collaboration between researchers and semiconductor industries to improve fabrication methods and reduce production cost. Future studies should also include practical testing under real-world computing environments instead of depending mainly on theoretical analysis.

Zahoor et al. (2020) discussed the structure, materials, and switching mechanisms of RRAM technology. The authors explained that RRAM offers high speed, low power consumption, and excellent scalability. However, the study placed heavy focus on technical material properties while giving less attention to long-term reliability problems such as endurance degradation, device variability, and data retention errors. In practical applications, memory systems are expected to perform consistently for many years, especially in servers and enterprise systems. The absence of detailed reliability testing reduces the strength of the conclusions presented in the study. To solve this problem, future research should include large-scale endurance experiments, thermal stability analysis, and error correction techniques that can improve the lifespan of RRAM devices. Intelligent memory controllers and advanced wear-leveling algorithms may also help reduce reliability problems in future RRAM systems.

Worledge and Hu (2024) examined Spin-Transfer Torque Magnetoresistive RAM (STT-MRAM) and described it as one of the most promising alternatives to traditional SRAM and DRAM technologies. The study highlighted the benefits of MRAM, including non-volatility, low standby power, and high-speed operation. Despite these advantages, the authors did not sufficiently discuss the high write energy and thermal stability problems associated with MRAM systems. In high-performance environments, thermal instability may reduce memory reliability and increase

operational errors. In addition, MRAM still faces manufacturing complexity due to the magnetic materials used during production. A possible solution is the development of improved magnetic materials with lower switching energy and better temperature resistance. Researchers can also combine MRAM with advanced cooling systems and energy-efficient architectures to improve overall stability.

Xie (2018) focused on emerging non-volatile memories and their impact on computer architecture design. The study explained how advanced memories could reduce the memory wall problem by improving bandwidth and lowering latency. Although the paper successfully explained architectural improvements, it did not fully consider software-level limitations. Hardware improvements alone cannot completely solve memory bottlenecks because software optimization also plays an important role in memory performance. Many operating systems and applications still use traditional memory management methods that are not optimized for modern memory technologies. To address this issue, researchers should develop memory-aware software systems, intelligent scheduling algorithms, and operating systems designed specifically for hybrid memory architectures.

Wang et al. (2023) investigated Computing-in-Memory (CIM) architectures using RRAM technology for artificial intelligence applications. The authors explained that CIM reduces data movement between processors and memory, thereby improving AI performance and energy efficiency. However, the study mainly focused on experimental AI workloads and did not fully examine large-scale commercial deployment challenges. The paper also lacked detailed analysis of hardware integration complexity and system compatibility with existing processor architectures. Although CIM shows strong promise, integrating these systems into traditional computer architectures remains difficult. A possible solution is the development of standardized memory interfaces and hybrid computing platforms that allow CIM technologies to work efficiently alongside traditional CPUs and GPUs.

Asad et al. (2022) reviewed memory subsystems for deep neural network accelerators and identified High Bandwidth Memory (HBM) as an important solution for AI systems. The study correctly emphasized the importance of high bandwidth in AI processing, but it paid limited attention to the high cost and heat generation associated with HBM systems. HBM technology requires complex 3D packaging and advanced cooling systems, which increase manufacturing expenses. This limits its affordability for many organizations and personal computing systems. Future solutions should focus on reducing production cost through improved fabrication techniques and developing energy-efficient cooling systems that can handle high thermal output more effectively.

Molas and Nowak (2021) reviewed several emerging memory technologies and explained their importance for artificial intelligence and big data applications. Although the study covered many advanced memory systems, it remained largely theoretical and lacked detailed performance comparisons under practical workloads. Different memory technologies behave differently depending

on the application environment, and theoretical analysis alone may not fully represent real-world performance. Future research should include benchmark testing across gaming systems, cloud servers, AI accelerators, and mobile devices to provide more practical evaluation of emerging RAM technologies.

Cheshmikhani et al. (2022) focused on improving the reliability of STT-MRAM cache systems by reducing error rates. While the proposed methods improved cache reliability, the study introduced additional architectural complexity that may increase system cost and design difficulty. Many advanced reliability techniques require extra circuitry, which can increase chip size and power usage. Future research should therefore focus on designing lightweight reliability mechanisms that provide error correction without significantly increasing hardware complexity.

Chen et al. (2016) compared several non-volatile memory technologies and concluded that MRAM, PCM, and RRAM are strong alternatives to traditional DRAM. Although the comparative review was informative, the study became less applicable over time because memory technology evolves rapidly. New generations of DDR memory, HBM systems, and AI-focused architectures have introduced additional performance improvements that were not covered in earlier reviews. Continuous updates and periodic review studies are therefore necessary to keep memory research relevant to current technological developments.

Le et al. (2025) discussed the memory wall problem in neuromorphic computing systems and explained how advanced memory technologies can improve processor-memory communication. While the study presented interesting future directions, neuromorphic computing is still largely experimental and not widely available in commercial systems. The paper provided limited discussion

on how these systems can be mass-produced or integrated into current computing infrastructure. To solve this issue, future research should focus on scalable neuromorphic hardware design and compatibility with existing semiconductor manufacturing processes.

Although different authors studied various aspects of RAM advancement, many studies share common limitations such as high implementation cost, limited real-world testing, scalability concerns, reliability problems, and insufficient software integration analysis. Solving these problems requires a combination of hardware and software improvements.

One important solution is the continued development of hybrid memory systems that combine the strengths of different memory technologies. For example, combining DRAM with MRAM or RRAM may improve both speed and energy efficiency while reducing cost. Hybrid architectures can also provide better balance between volatile and non-volatile storage systems.

Another solution involves improving semiconductor manufacturing techniques. Advanced fabrication technologies can help reduce defects, improve scalability, and lower production costs for emerging memory systems. The use of artificial intelligence in chip design may also improve memory optimization and reduce engineering complexity.

Software optimization is equally important. Operating systems, compilers, and applications should be redesigned to support modern memory architectures more efficiently. Intelligent memory scheduling, NUMA-aware memory allocation, and AI-driven resource management can help reduce latency and improve memory utilization.

Researchers should also continue exploring advanced cooling systems and low-power architectures to reduce heat generation and improve energy efficiency. Efficient thermal management is essential for high-performance computing systems such as AI accelerators and cloud data centers.

Finally, stronger collaboration between universities, semiconductor industries, and technology companies is necessary to accelerate the practical implementation of emerging RAM technologies. Many promising memory systems remain limited to research laboratories because of manufacturing and commercial challenges. Industrial collaboration can help bridge the gap between theoretical research and practical deployment.

In conclusion, previous authors have contributed significantly to the advancement of RAM technology by introducing new memory architectures and identifying major performance challenges. However, many studies still face limitations related to cost, scalability, reliability, and practical implementation. Future solutions should combine advanced hardware design, intelligent software

optimization, improved manufacturing methods, and industrial collaboration to develop faster, more reliable, and energy-efficient memory systems capable of supporting next-generation computing applications.

SUMMARY

This study reviewed the advancement of RAM technology and examined how memory systems have evolved from traditional SRAM and DRAM to modern and emerging technologies such as DDR5, High Bandwidth Memory (HBM), Magnet or resistive RAM (MRAM), Resistive RAM (RRAM), and Phase Change Memory (PCM). The review showed that the increasing demand for high performance computing, artificial intelligence, cloud computing, gaming, and big data analytics has pushed researchers to develop faster, more reliable, and energy-efficient memory systems.

The study discussed major challenges affecting RAM technology, including the memory wall problem, high power consumption, latency, heat generation, scalability limitations, manufacturing complexity, and reliability issues. Several researchers proposed different solutions to these problems through advanced memory architectures, non-volatile memory technologies, computing-in-memory systems, intelligent memory controllers, and improved cooling systems.

The literature review also analyzed the contributions and limitations of different authors. While many researchers successfully explained the advantages of emerging memory technologies, some studies focused mainly on theoretical analysis without fully addressing practical implementation challenges such as production cost, thermal management, industrial scalability, compatibility with existing systems, and long term reliability. The review further revealed that emerging technologies such as MRAM, RRAM, PCM, and HBM have strong potential for future computing systems, especially in artificial intelligence and high performance computing environments.

The discussion additionally highlighted the importance of combining both hardware and software solutions to

improve memory performance. Techniques such as cache optimization, parallel processing, Processing in Memory (PIM), Computing-in-Memory (CIM), error correction methods, and hybrid memory architectures were identified as important solutions for reducing latency, improving bandwidth, lowering energy consumption, and solving memory bottlenecks.

CONCLUSION

The advancement of RAM technology has become essential for supporting modern computing applications that require high speed, large memory capacity, and energy efficiency. Traditional memory systems such as SRAM and DRAM have contributed greatly to computer development, but they now face limitations in power consumption, scalability, latency, and reliability. To overcome these problems, researchers have developed advanced memory technologies including DDR5, HBM, MRAM, RRAM, and PCM.

This review showed that emerging memory technologies provide important improvements in bandwidth, processing speed, energy efficiency, and non-volatile storage capabilities. Technologies such as HBM and DDR5 improve data transfer performance, while MRAM, RRAM, and PCM

offer low-power and high-speed alternatives to traditional memory systems. In addition, modern approaches such as Processing-in-Memory and neuromorphic computing are helping reduce the memory wall problem by minimizing data movement between processors and memory.

However, despite these advancements, several challenges still remain. High manufacturing cost, heat generation, reliability concerns, scalability limitations, and integration complexity continue to affect the widespread adoption of emerging memory technologies. Many studies also lack sufficient practical testing under real-world conditions, which creates gaps between theoretical research and industrial implementation.

To address these challenges, future research should focus on improving semiconductor manufacturing techniques, developing energy-efficient architectures, enhancing software optimization, and creating hybrid memory systems that combine the strengths of different memory technologies. Strong collaboration between researchers, universities, and semiconductor industries will also be important for transforming experimental memory technologies into commercially successful products.

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